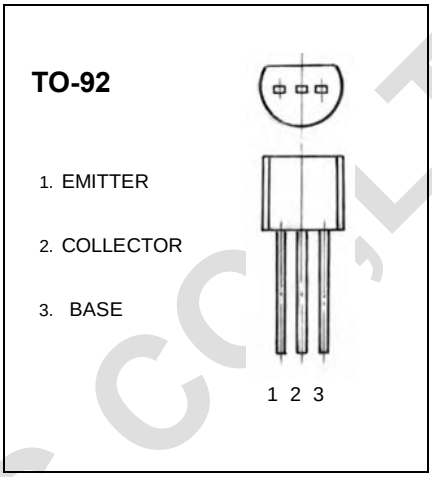
2SC388 TRANSISTOR (NPN)



FEATURES

Power dissipation

P_{CM}: 0.3 W (Tamb=25℃)

Collector current

I_{CM}: 50 mA

Collector-base voltage

$V_{(BR)CBO}$: 30 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=10μA, I_E=0	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=5mA, I_B=0	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	4			V
Collector cut-off current	I_{CBO}	V_{CB}=30V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=3V, I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=12.5V, I_C=12.5mA	20		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=15mA, I_B=1.5mA			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=15mA, I_B=1.5mA			1.2	V
Transition frequency	f_T	V_{CE}=12.5V, I_C=12.5mA	300			MHz
Collector output capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	0.8		2	pF
Power Gain	Gpe	V_{CC}=12.5V, I_c=12.5mA, f=45MHZ	28		36	dB

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